



## YJD40P03B

### P-Channel Enhancement Mode Field Effect Transistor

#### Product Summary

$V_{DS}$	-30 V
$I_D$	-40 A
$R_{DS(ON)}$ ( at $V_{GS}=-10V$ )	14 m
$R_{DS(ON)}$ ( at $V_{GS}=-4.5V$ )	22 m
100% EAS Tested	
100% $V_{DS}$ Tested	

#### General Description

Trench Power LV MOSFET technology  
High density cell design for Low  $R_{DS(ON)}$   
High Speed switching

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reW\*nBT/F5 5.52 T TJETQq0.000008882 0 596.04 842.04 reW\*nBT/F5



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## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-$	-30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	
		$V_{DS}=-30V, V_{GS}=0V, T_J=150$	-	-	-100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-$	-1	-1.5	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-20A$	-	10.5	14	
		$V_{GS}=-4.5V, I_D=-20A$	-	16	22	
Diode Forward Voltage	$V_{SD}$	$I_S=-20A, V_{GS}=0V$	-	-0.9	-1.3	V
Gate resistance	$R_G$	$f=1MHz$				



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## Typical Electrical and Thermal Characteristics Diagrams

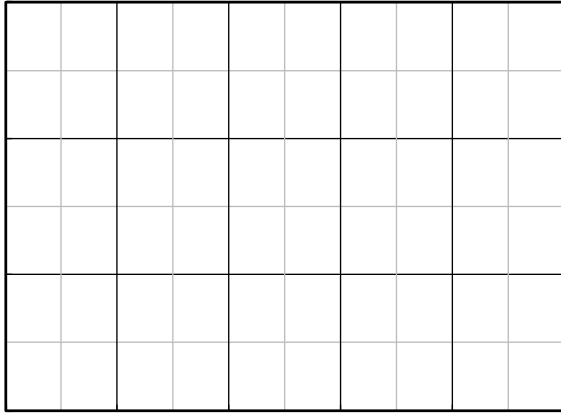


Figure 1. Output Characteristics

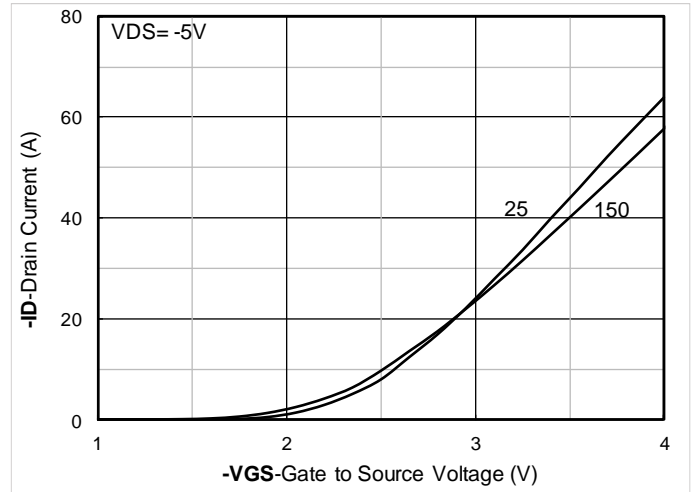


Figure 2. Transfer Characteristics

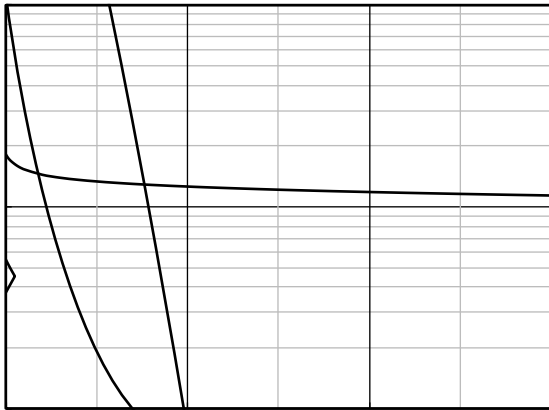


Figure 3. Capacitance Characteristics

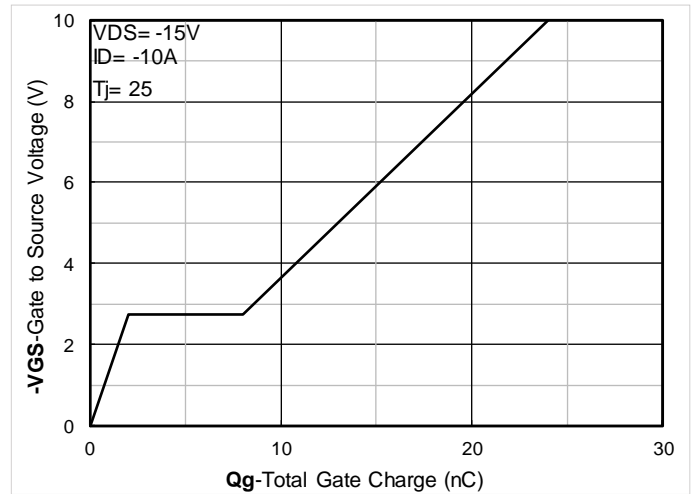


Figure 4. Gate Charge

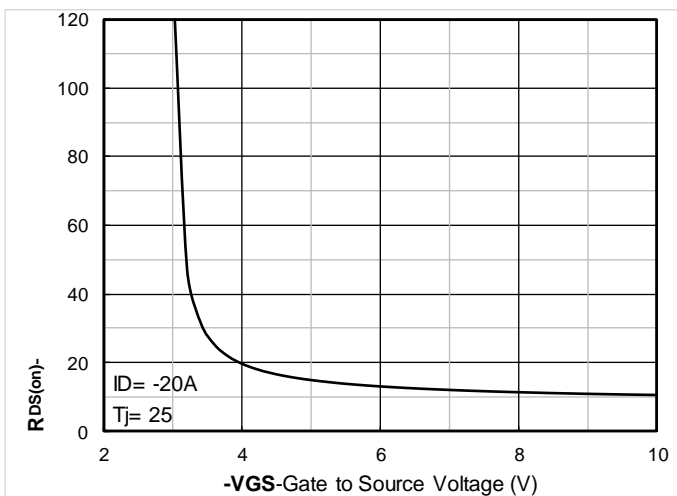


Figure 5. On-Resistance vs Gate to Source Voltage

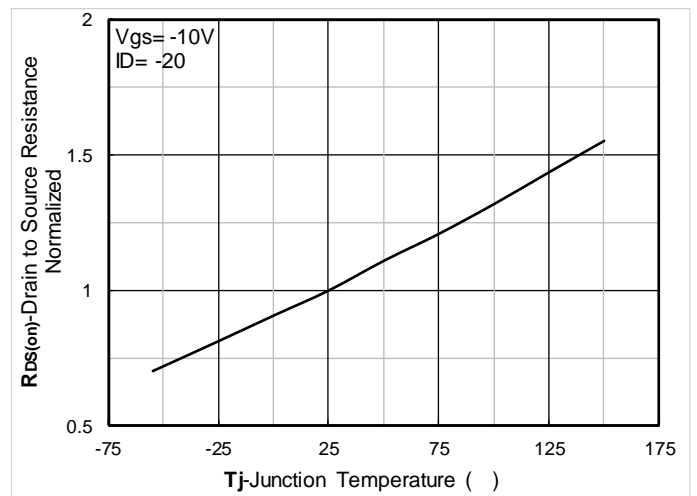


Figure 6. Normalized On-Resistance

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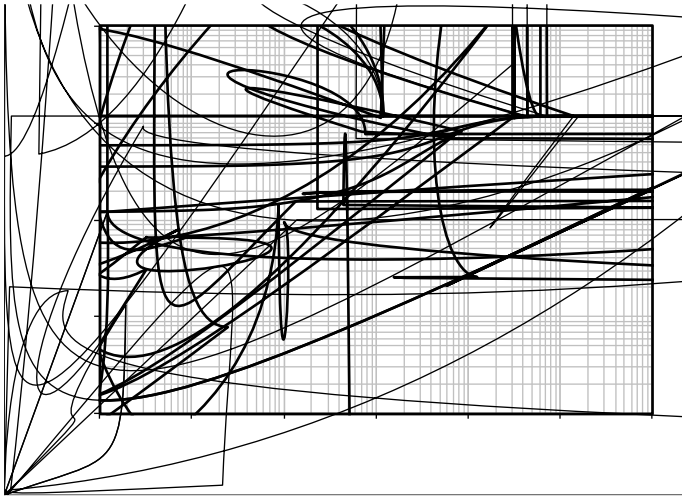


Figure 13. Maximum Transient Thermal Impedance

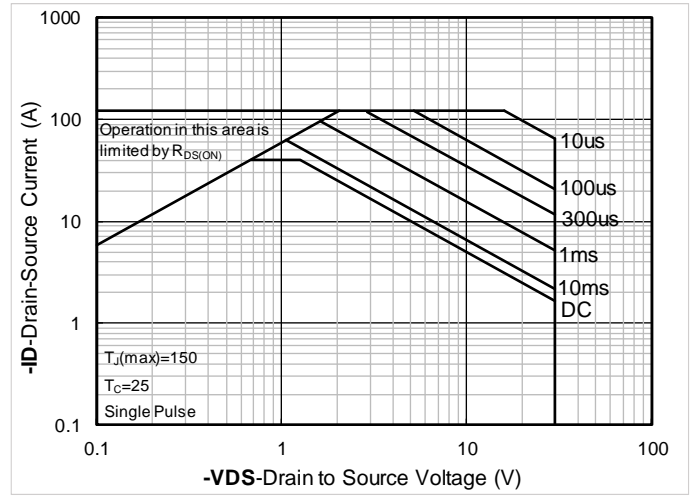


Figure 14.





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